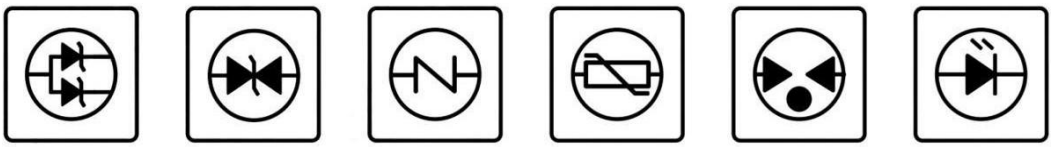
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MSZ0D10A

Product specification

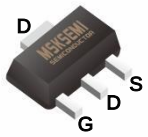
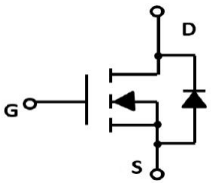
MSZ0D10A

30V/10A N-Channel MOSFET

Features

- Trench Power LV MOSFET technology
- High density cell design for low $R_{DS(ON)}$
- High Speed switching

Reference News

SOT-89-3L	Schematic diagram	Marking
		0D10A ****

Application

- Battery protection
- Load switch
- Power management

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
30V	15mΩ@10V	10A
	20mΩ@4.5V	

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage		30	V
V_{GS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-50 to 155	°C
I_S	Diode Continuous Forward Current	Tc=25°C	10	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	Tc=25°C	40	A
I_D	Continuous Drain Current	Tc=25°C	10	A
P_D	Maximum Power Dissipation	Tc=25°C	1.5	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		104	°C/W

Ordering Information (Example)

Type	Package	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MSZ0D10A	SOT-89-3L	1,000	4,000	24,000	7"reel

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Electrical Characteristics (TJ=25℃ unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$BV_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V，I_D=250μA	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V，V_{GS}=0V	--	--	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V，V_{DS}=0V	--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}，I_D=250μA	1.0	1.45	2.5	V
$R_{DS(on)}$	Drain-Source On-State Resistance	V_{GS}=10V，I_D=5.8A	--	15	20	mΩ
		V_{GS}=4.5V，I_D=5.0A	--	20	30	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C_{ISS}	Input Capacitance	V_{DS}=15V，V_{GS}=0V，f=1MHz	--	632	--	pF
C_{OSS}	Output Capacitance		--	58	--	pF
C_{RSS}	Reverse Transfer Capacitance		--	70	--	pF
Switching Characteristics						
Q_g	Total Gate Charge	V_{DS}=15V，I_D=10A，V_{GS}=10V	--	17.3	--	nC
Q_{gs}	Gate Source Charge		--	2.2	--	nC
Q_{gd}	Gate Drain Charge		--	2.1	--	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=15V，I_D=10A，V_{GS}=10V，R_G=3Ω	--	4.4	--	nS
t_r	Turn-on Rise Time		--	28.3	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	16.5	--	nS
t_f	Turn-Off Fall Time		--	26.3	--	nS
Source- Drain Diode Characteristics						
V_{SD}	Forward on voltage	Tj=25℃， Is=10A	--	--	1.2	V

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Typical Operating Characteristics

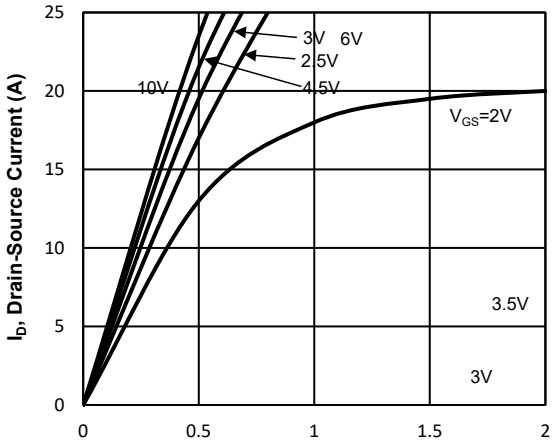


Fig1. Typical Output Characteristics

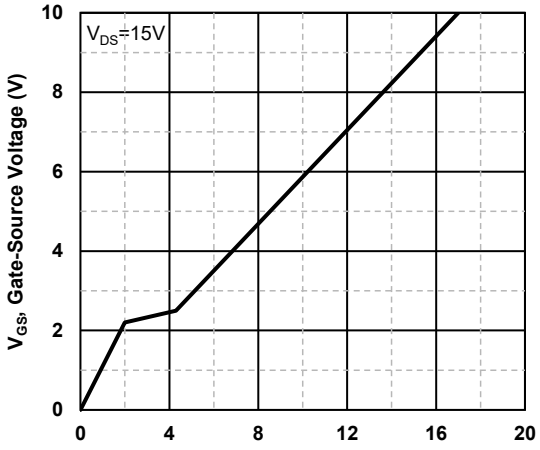


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

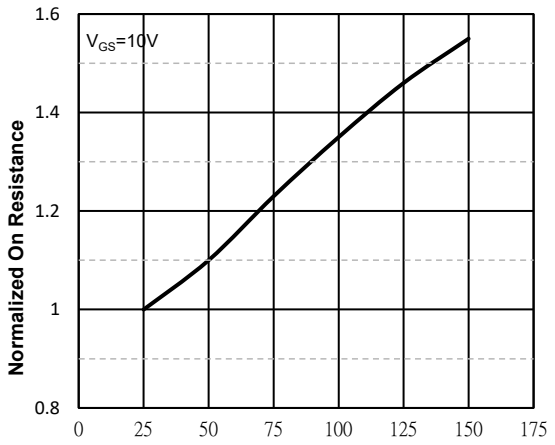


Fig3. Normalized On-Resistance Vs. Temperature

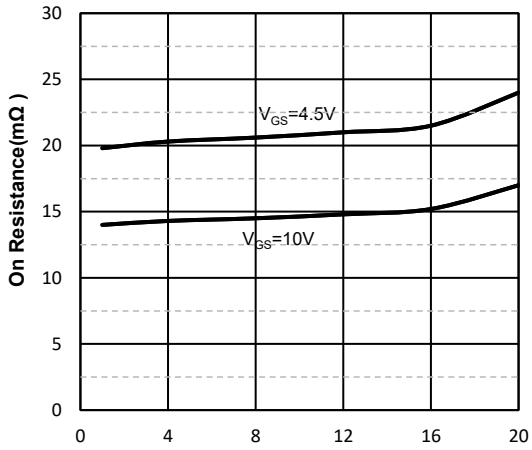


Fig4. On-Resistance Vs. Drain-Source Current

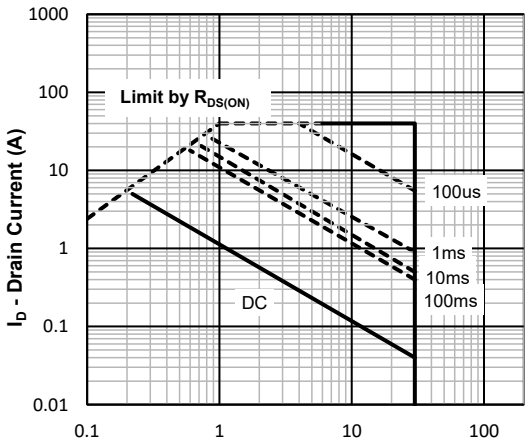


Fig5. Maximum Safe Operating Area

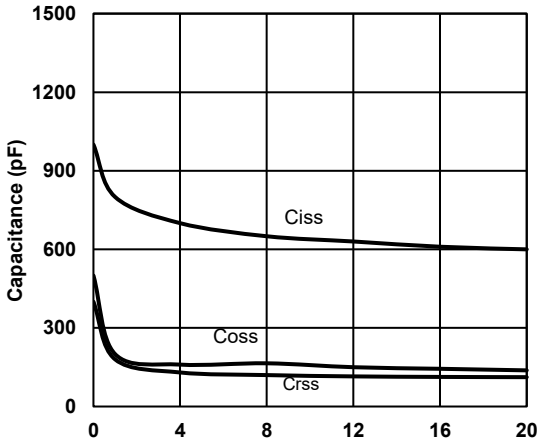
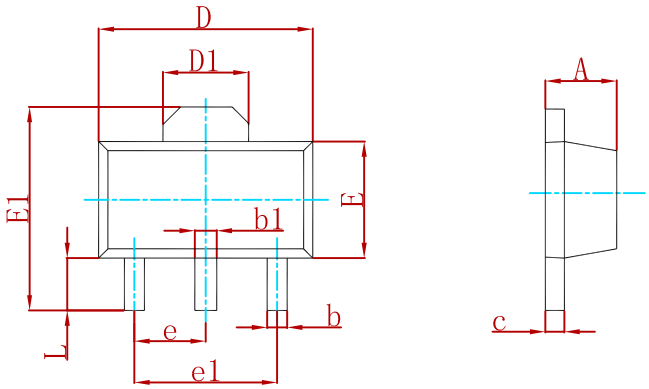


Fig6 Typical Capacitance Vs.Drain-Source Voltage

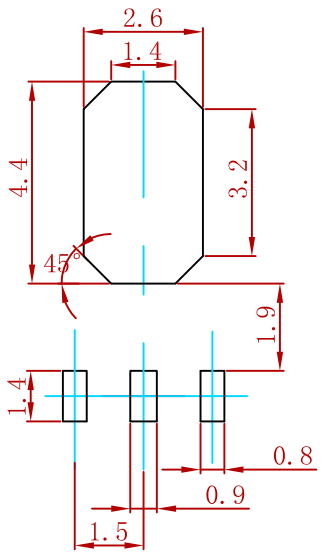
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PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

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